Analog Power AMR434N

# N-Channel 30-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

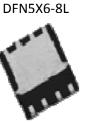
## **Typical Applications:**

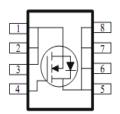
- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
30	22 @ V <sub>GS</sub> = 10V	12.4		
	26 @ V <sub>GS</sub> = 4.5V	11.4		



ROHS COMPLIANT HALOGEN FREE





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter				Limit	Units		
Drain-Source Voltage				30	V		
Gate-Source Voltage				±20	V		
Continuous Drain Coursent®	T <sub>A</sub> =25°0	T <sub>A</sub> =25°C	ı	12.4			
Continuous Drain Current <sup>a</sup>		T <sub>A</sub> =70°C	l <sub>D</sub>	9.9	Α		
Pulsed Drain Current <sup>b</sup>				30			
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	5.7	Α				
Davier Dissipation 8		T <sub>A</sub> =25°C	P <sub>D</sub>	5	W		
Power Dissipation <sup>a</sup>	T		' D	3.2	V V		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>sta</sub>	-55 to 150	°C				

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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### **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	1 10		uA		
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$					
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	18			Α	
	r	$V_{GS} = 10 \text{ V}, I_D = 9.8 \text{ A}$			22		
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 7.9 \text{ A}$			26	mΩ	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 9.8 \text{ A}$		4		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2.8 \text{ A}, V_{GS} = 0 \text{ V}$		0.86		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		5.9		nC	
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 9.8 \text{ A}$		2.7			
Gate-Drain Charge	$Q_gd$	1 <sub>D</sub> = 3.0 A		2.7			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 15 \text{ V}, R_1 = 1.6 \Omega,$		5			
Rise Time	t <sub>r</sub>	$V_{DS} = 15 \text{ V}, \text{ K}_{L} - 1.0 \Omega,$ $I_{D} = 9.8 \text{ A},$		5		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		15			
Fall Time	t <sub>f</sub>	V GEN = 10 V, 1 (GEN = 0.12		5			
Input Capacitance	C <sub>iss</sub>			525			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		64		pF	
Reverse Transfer Capacitance	$C_{rss}$			48			

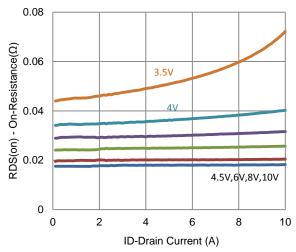
#### Notes

- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

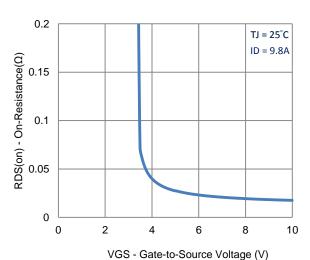
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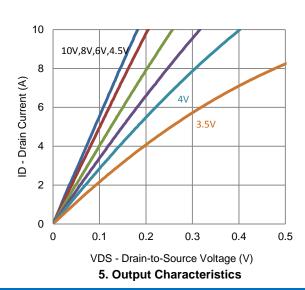
## **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



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TJ = 25°C

8

(Y)

tuesing

4

0

0

1

2

0

1

2

3

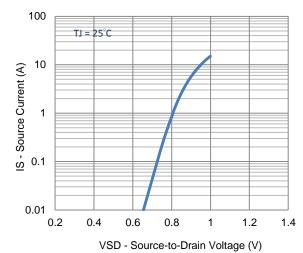
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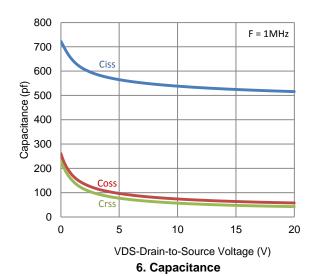
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VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

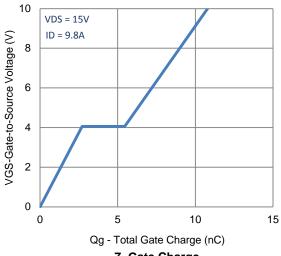


4. Drain-to-Source Forward Voltage

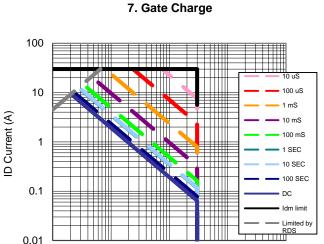


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## **Typical Electrical Characteristics**



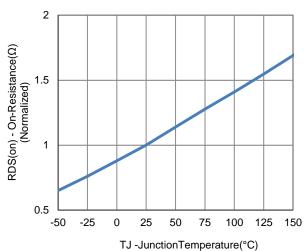
1000



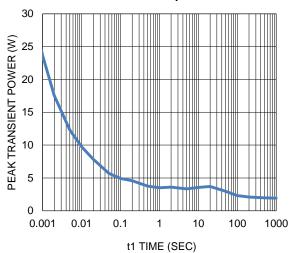
VDS Drain to Source Voltage (V) 9. Safe Operating Area

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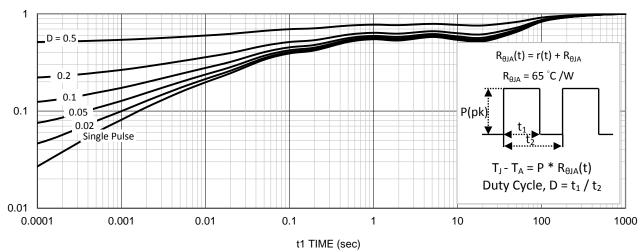
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8. Normalized On-Resistance Vs **Junction Temperature** 



10. Single Pulse Maximum Power Dissipation

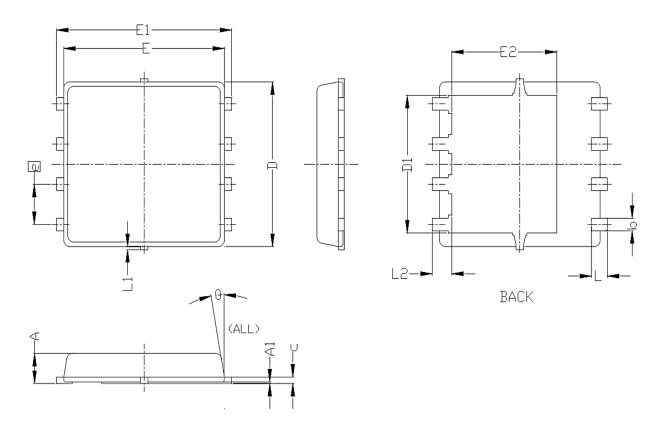


11. Normalized Thermal Transient Junction to Ambient

0.1

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# Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0. 15	0. 20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е	5, 55 BSC				0. 219 BSC		
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	

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